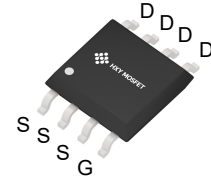




Description

The SI4812BDY-T1-GE3 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

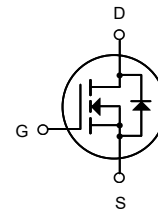


SOP-8
(SO-8)

General Features

$V_{DS} = 30V$ $I_D = 8.5A$

$R_{DS(ON)} < 18m\Omega$ @ $V_{GS}=10V$



N-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Ordering Information

| Product ID | Pack | Brand | Qty(PCS) |
|------------------|-------------|------------|----------|
| SI4812BDY-T1-GE3 | SOP-8(SO-8) | HXY MOSFET | 3000 |

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

| Symbol | Parameter | Rating | Units |
|----------------------|---|------------|--------------|
| V_{DS} | Drain-Source Voltage | 30 | V |
| V_{GS} | Gate-Source Voltage | ± 20 | V |
| $I_D@T_A=25^\circ C$ | Continuous Drain Current ¹ | 8.5 | A |
| $I_D@T_A=70^\circ C$ | Continuous Drain Current ¹ | 5.6 | A |
| I_{DM} | Pulsed Drain Current ² | 35 | A |
| EAS | Single Pulse Avalanche Energy ³ | 20 | mJ |
| I_{AS} | Avalanche Current | 20 | A |
| $P_D@T_A=25^\circ C$ | Total Power Dissipation ⁴ | 1.5 | W |
| T_{STG} | Storage Temperature Range | -55 to 150 | $^\circ C$ |
| T_J | Operating Junction Temperature Range | -55 to 150 | $^\circ C$ |
| $R_{\theta JA}$ | Thermal Resistance Junction-ambient ¹ ($t \leq 10s$) | 85 | $^\circ C/W$ |
| | Thermal Resistance Junction-ambient ¹ | 25 | $^\circ C/W$ |



Electrical Characteristics (T_J=25°C, unless otherwise noted)

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Unit |
|-------------------------------------|--|--|------|-------|-------|-------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =250μA | 30 | --- | --- | V |
| ΔBV _{DSS} /ΔT _J | BVDSS Temperature Coefficient | Reference to 25°C, I _D =1mA | --- | 0.034 | --- | V/°C |
| R _{DS(ON)} | Static Drain-Source On-Resistance ² | V _{GS} =10V, I _D =7A | --- | 14 | 18 | mΩ |
| | | V _{GS} =4.5V, I _D =4A | --- | 20 | 26 | |
| V _{GS(th)} | Gate Threshold Voltage | V _{GS} =V _{DS} , I _D =250μA | 1.2 | 1.5 | 2.5 | V |
| ΔV _{GS(th)} | V _{GS(th)} Temperature Coefficient | | --- | -3.84 | --- | mV/°C |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =24V, V _{GS} =0V, T _J =25°C | --- | --- | 1 | μA |
| | | V _{DS} =24V, V _{GS} =0V, T _J =55°C | --- | --- | 5 | |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} =±20V, V _{DS} =0V | --- | --- | ±100 | nA |
| g _{fs} | Forward Transconductance | V _{DS} =5V, I _D =7A | --- | 6.2 | --- | S |
| R _g | Gate Resistance | V _{DS} =0V, V _{GS} =0V, f=1MHz | --- | 1.04 | 2.1 | Ω |
| Q _g | Total Gate Charge (4.5V) | V _{DS} =15V, V _{GS} =4.5V, I _D =7A | --- | 6 | 8.4 | nC |
| Q _{gs} | Gate-Source Charge | | --- | 2.2 | 3.1 | |
| Q _{gd} | Gate-Drain Charge | | --- | 2 | 2.8 | |
| T _{d(on)} | Turn-On Delay Time | V _{DD} =15V, V _{GS} =10V, R _G =3.3Ω I _D =7A | --- | 1.2 | 2.4 | ns |
| T _r | Rise Time | | --- | 40 | 72.0 | |
| T _{d(off)} | Turn-Off Delay Time | | --- | 18 | 36.0 | |
| T _f | Fall Time | | --- | 7.2 | 14.4 | |
| C _{iss} | Input Capacitance | V _{DS} =15V, V _{GS} =0V, f=1MHz | --- | 583 | 816.2 | pF |
| C _{oss} | Output Capacitance | | --- | 77 | 107.8 | |
| C _{rss} | Reverse Transfer Capacitance | | --- | 59 | 82.6 | |
| I _S | Continuous Source Current ^{1,5} | V _G =V _D =0V, Force Current | --- | --- | 7 | A |
| I _{SM} | Pulsed Source Current ^{2,5} | | --- | --- | 35 | A |
| V _{SD} | Diode Forward Voltage ² | V _{GS} =0V, I _S =1A, T _J =25°C | --- | --- | 1.2 | V |
| t _{rr} | Reverse Recovery Time | I _F =7A, dI/dt=100A/μs, T _J =25°C | --- | 7.2 | --- | nS |
| Q _{rr} | Reverse Recovery Charge | | --- | 2.9 | --- | nC |

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
3. The EAS data shows Max. rating. The test condition is V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=20A
4. The power dissipation is limited by 150°C junction temperature
5. The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.



Typical Characteristics

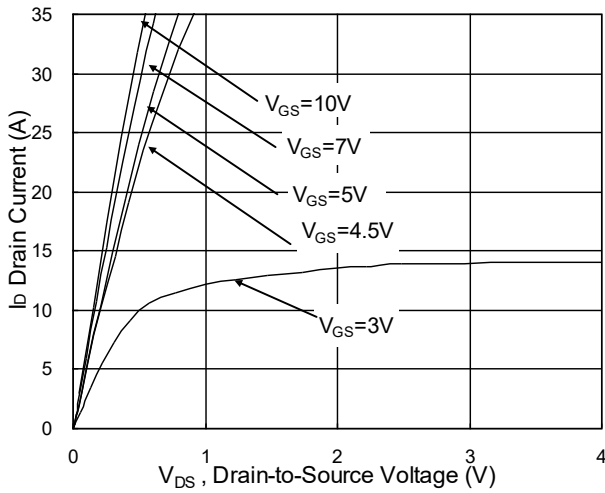


Fig.1 Typical Output Characteristics

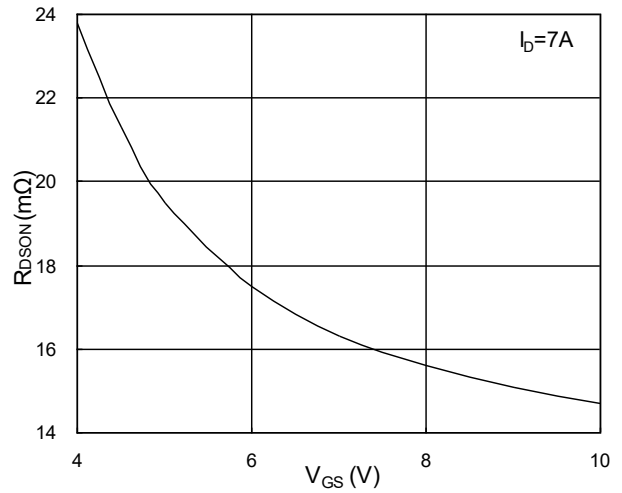


Fig.2 On-Resistance vs. Gate-Source

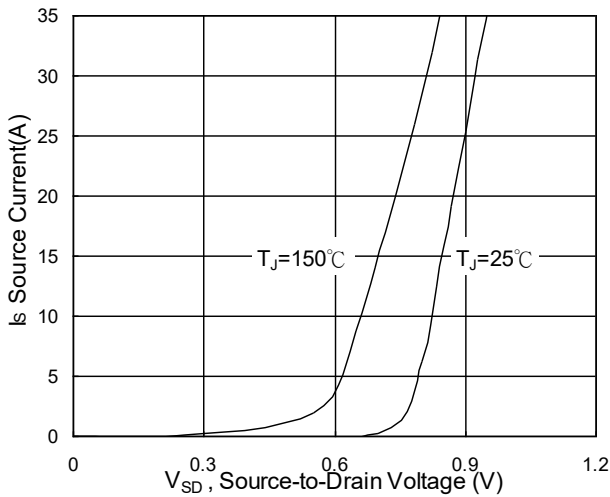


Fig.3 Forward Characteristics Of Reverse

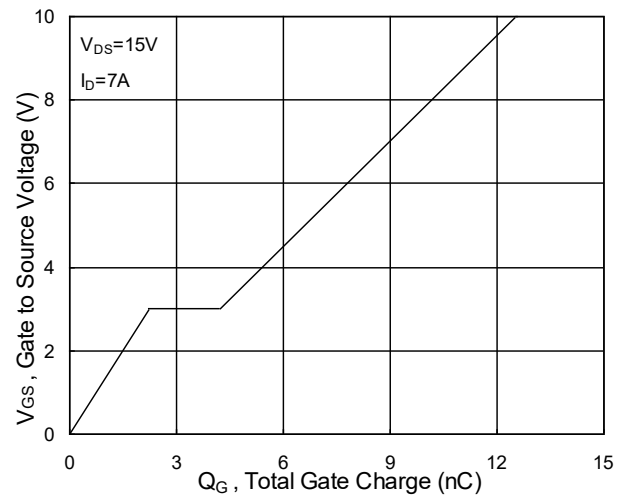


Fig.4 Gate-Charge Characteristics

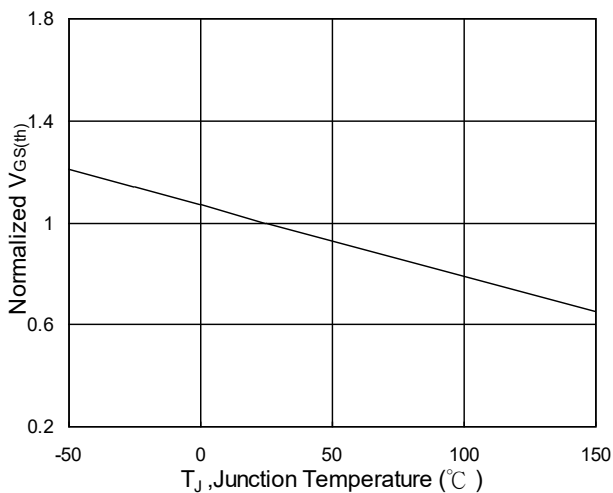


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

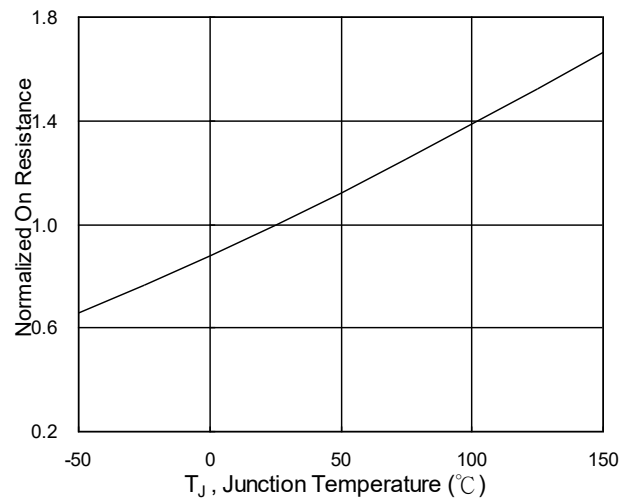


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

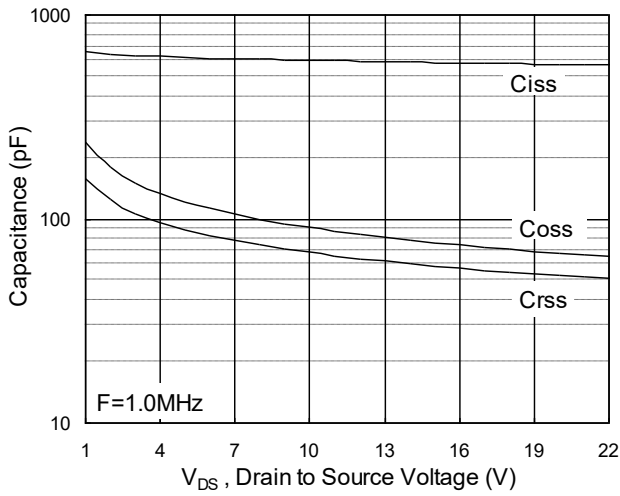


Fig.7 Capacitance

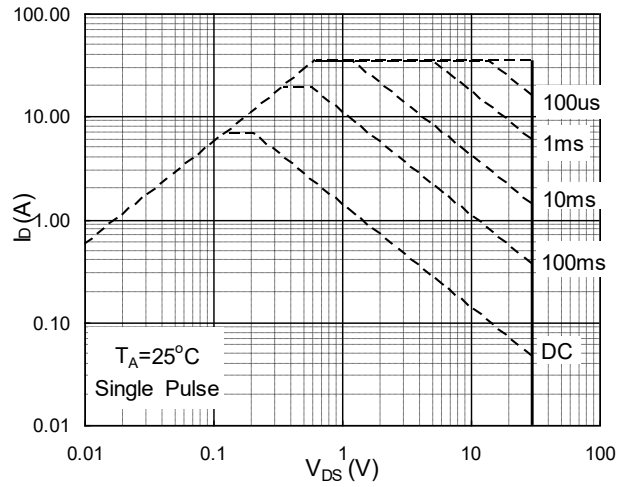


Fig.8 Safe Operating Area

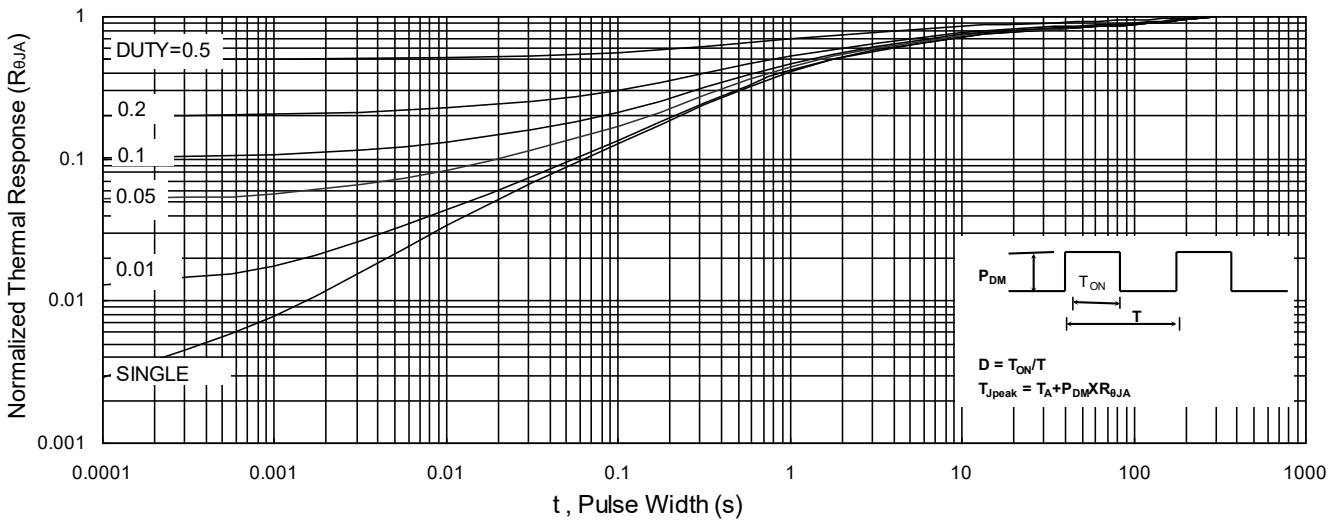


Fig.9 Normalized Maximum Transient Thermal Impedance

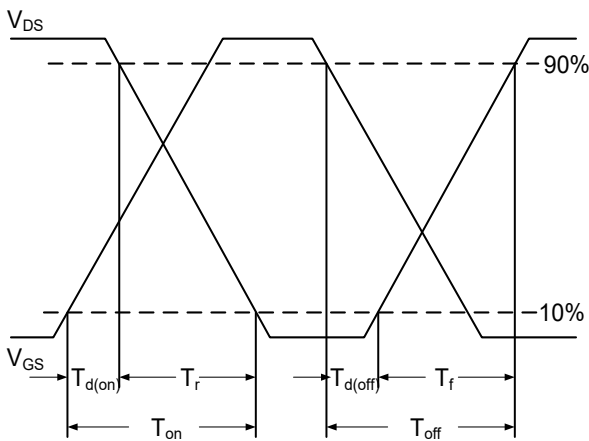


Fig.10 Switching Time Waveform

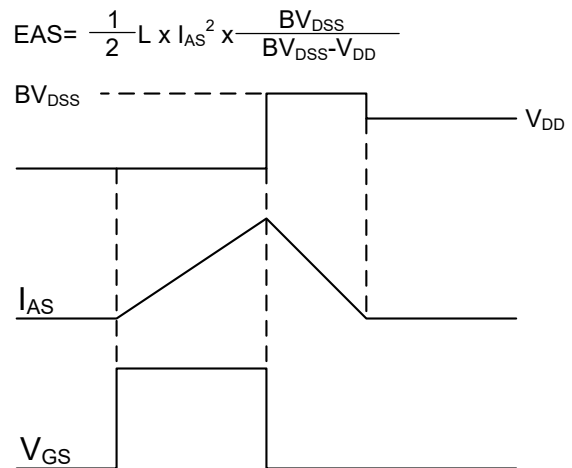


Fig.11 Unclamped Inductive Switching Waveform



SOP-8(SO-8) Package Outline Dimensions



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min | Max | Min | Max |
| A | 1.350 | 1.750 | 0.053 | 0.069 |
| A1 | 0.100 | 0.250 | 0.004 | 0.010 |
| A2 | 1.350 | 1.550 | 0.053 | 0.061 |
| b | 0.330 | 0.510 | 0.013 | 0.020 |
| c | 0.170 | 0.250 | 0.007 | 0.010 |
| D | 4.800 | 5.000 | 0.189 | 0.197 |
| e | 1.270 (BSC) | | 0.050 (BSC) | |
| E | 5.800 | 6.200 | 0.228 | 0.244 |
| E1 | 3.800 | 4.000 | 0.150 | 0.157 |
| L | 0.400 | 1.270 | 0.016 | 0.050 |
| θ | 0° | 8° | 0° | 8° |



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.



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